2N7000 Power MOSFET

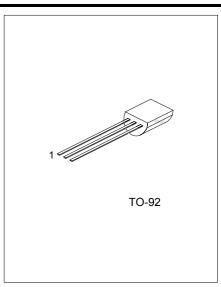
N-CHANNEL ENHANCEMENT MODE

■ DESCRIPTION

The UTC **2N7000** has been designed to minimize on-state resistance while provide rugged, reliable, and fast switching performance. It can be used in most applications requiring up to 400mA DC and can deliver pulsed currents up to 2A. The product is particularly suited for low voltage, low current applications such as small servo motor control, power MOSFET gate drivers, and other switching applications

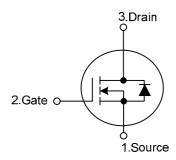
■ FEATURES

- *High density cell design for low R_{DS(ON)}
- *Voltage controlled small signal switch
- *Rugged and reliable
- *High saturation current capability



*Pb-free plating product number:2N7000L

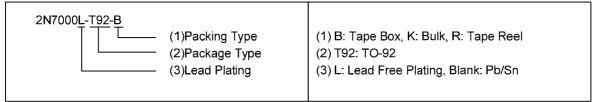
■ SYMBOL



■ ORDERING INFORMATION

Order Number		Dookogo	Pin Assignment			Dooking	
Normal	Lead Free Plating	Package	1	2	3	Packing	
2N7000-T92-B	2N7000L-T92-B	TO-92	S	G	D	Tape Box	
2N7000-T92-K	2N7000L-T92-K	TO-92	S	G	D	Bulk	
2N7000-T92-R	2N7000L-T92-R	TO-92	S	G	D	Tape Reel	

Note: Pin Assignment: G: Gate D: Drain S: Source



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■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V _{DSS}	60	V
Drain-Gate Voltage (R _{GS} ≤1MΩ)		V_{DGR}	60	V
Gate -Source Voltage	Continuous	V _{GS}	±20	V
Gate -Source voltage	Non Repetitive (tp<50)	s) VGS	±40	V
Maximum Drain Current Continuou			115	mA
Maximum Drain Current	Pulsed	ID	GR 60 ±20 ±40 115 0 800 0 3.2 n	mA
Maximum Power Dissipation	pation		400	mW
erated above 25°C		P _D	3.2	mW/°C
Operating and Storage Temperature		$T_{J,}T_{STG}$	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

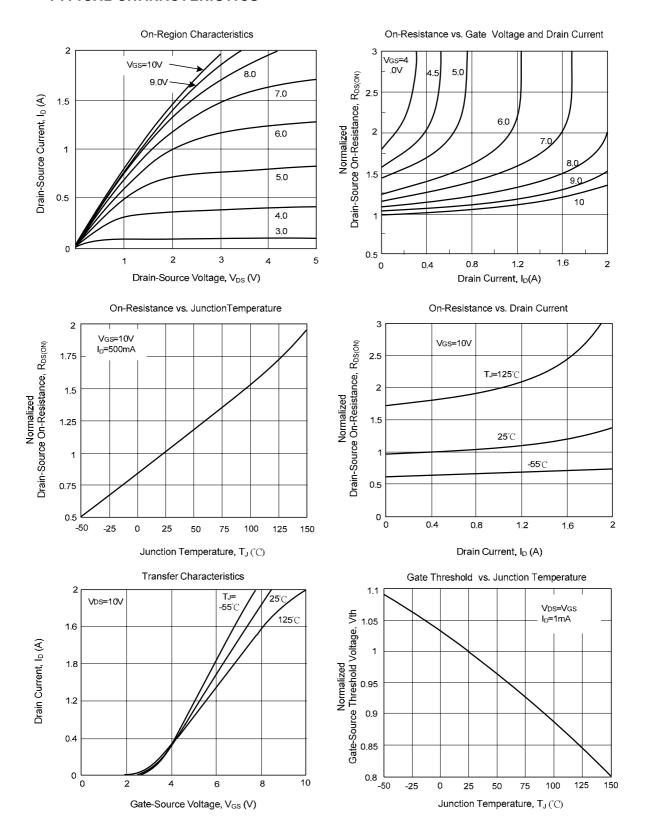
PARAMETER	SYMBOL	RATINGS	UNIT
Junction-to-Ambient	$\theta_{\sf JA}$	312.5	°C/W

■ ELECTRICAL CHARACTERISTICS (Ta =25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS	_				_		
Drain-Source Breakdown Voltage	BV _{DSS}	V_{GS} =0 V , I_D =10 μ A	60			V	
Drain-Source Leakage Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V			1	μA	
Dialii-Source Leakage Current		T _J =125°C			0.5	mA	
Gate-Body leakage, Forward	I _{GSSF}	V _{GS} =20V, V _{DS} =0V			100	nA	
Gate-Body leakage Reverse	I _{GSSR}	V _{GS} =-20V, V _{DS} =0V			-100	nA	
ON CHARACTERISTICS (Note)							
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	1	2.1	2.5	V	
		V _{GS} =10V, I _D =500mA		1.2	7.5	- Ω	
Static Drain-Source On-Resistance	Dagger	T _J =100°C		1.7	13.5		
Static Dialit-Source Off-Resistance	R _{DS(ON)}	V_{GS} =5.0V, I_D =50mA		1.7	7.5		
		T _J =100°C		2.4	13.5		
Drain-Source On-Voltage	V _{DS(ON)}	$V_{GS} = 10V, I_D = 500mA$		0.6	3.75	V	
	V DS(ON)	V _{GS} = 5.0V, I _D =50mA		0.09	1.5		
On-State Drain Current	I _{D(ON)}	V_{GS} =10V, $V_{DS} \ge 2V_{DS(ON)}$	500	2700		mA	
DYNAMIC CHARACTERISTICS							
Input Capacitance	C _{ISS}			20	50	pF	
Output Capacitance	Coss	V _{DS} =25V,V _{GS} =0V, f=1.0MHz		11	25	pF	
Reverse Transfer Capacitance	C _{RSS}	1		4	5	pF	
Turn On Time		V_{DD} =30V, R_L =150 Ω ,			20		
Turn-On Time	t _{ON}	I_D =200mA, V_{GS} =10V, R_{GEN} =25 Ω			20	ns	
Turn-Off Time	t _{OFF}	V_{DD} =30V, R_L =150 Ω , I_D =200mA,			20	ns	
Turi-On Time		V_{GS} =10V, R_{GEN} =25 Ω			20	115	
DRAIN-SOURCE DIODE CHARACT	ERISTICS A	AND MAXIMUM RATINGS					
Drain-Source Diode Forward	V_{SD}	\/O\/_Is=115m\/\Noto\		0.88	1.5	V	
oltage		V _{GS} =0V, Is=115mA(Note)		0.00	1.5	V	
Maximum Continuous Drain-Source	ls				115	mA	
Diode Forward Current	IS			1	115	IIIA	
Maximum Pulsed Drain-Source	I _{SM}				0.8	Α	
Diode Forward Current					0.0		

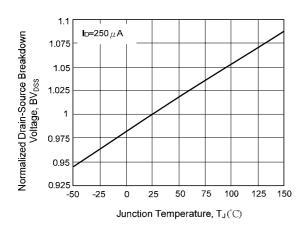
Note: Pulse Test: Pulse Width≤300µs, Duty Cycle≤2.0%

■ TYPICAL CHARACTERISTICS

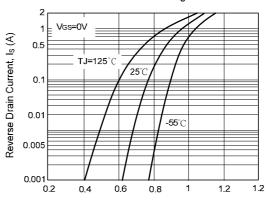


■ TYPICAL CHARACTERISTICS(Cont.)

Breakdown Voltage vs. Junction Temperature

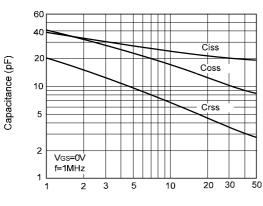


Reverse Drain Current vs. Body Diode Forward Voltage

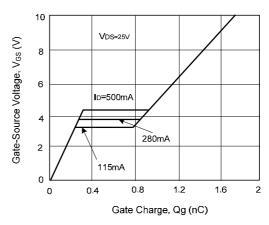


Body Diode Forward Voltage, V_{SD} (V)

Capacitance Characteristics

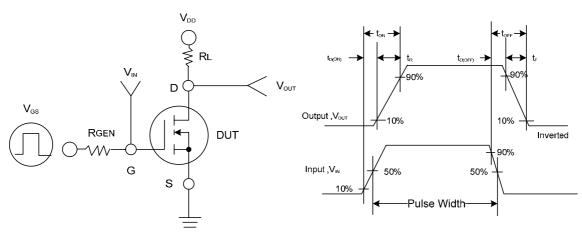


Gate Charge Characteristics



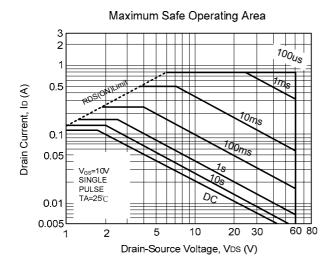
Drain-Source Voltage, V_{DS} (V)

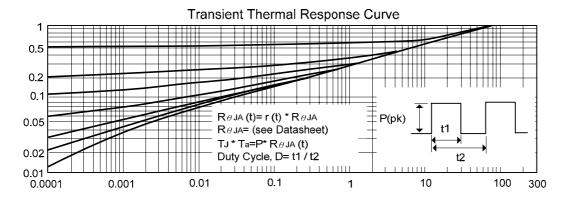
Switching Waveforms



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■ TYPICAL CHARACTERISTICS(Cont.)





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